

ZXMN3A01F

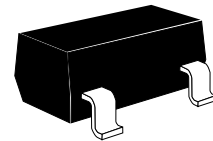
30V N-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = 30V$; $R_{DS(ON)} = 0.12\Omega$ $I_D = 2.0A$

DESCRIPTION

This new generation of TRENCH MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



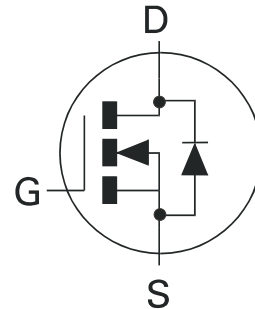
SOT23

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT23 package

APPLICATIONS

- DC - DC Converters
- Power Management Functions
- Motor control

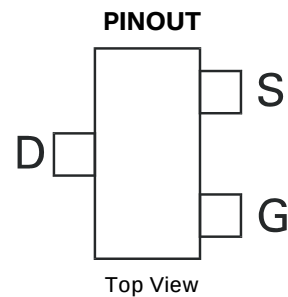


ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMN3A01FTA	7"	8mm	3000 units
ZXMN3A01FTC	13"	8mm	10000 units

DEVICE MARKING

- 7N3



ZXMN3A01F

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	30	V
Gate Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $V_{GS}=10V$; $T_A=25^{\circ}C$ (b) $V_{GS}=10V$; $T_A=70^{\circ}C$ (b) $V_{GS}=10V$; $T_A=25^{\circ}C$ (a)	I_D	2.0 1.6 1.8	A
Pulsed Drain Current (c)	I_{DM}	8	A
Continuous Source Current (Body Diode) (b)	I_S	1.3	A
Pulsed Source Current (Body Diode) (c)	I_{SM}	8	A
Power Dissipation at $T_A=25^{\circ}C$ (a) Linear Derating Factor	P_D	625 5	mW mW/ $^{\circ}C$
Power Dissipation at $T_A=25^{\circ}C$ (b) Linear Derating Factor	P_D	806 6.4	mW mW/ $^{\circ}C$
Operating and Storage Temperature Range	$T_J:T_{stg}$	-55 to +150	$^{\circ}C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	200	$^{\circ}C/W$
Junction to Ambient (b)	$R_{\theta JA}$	155	$^{\circ}C/W$

NOTES

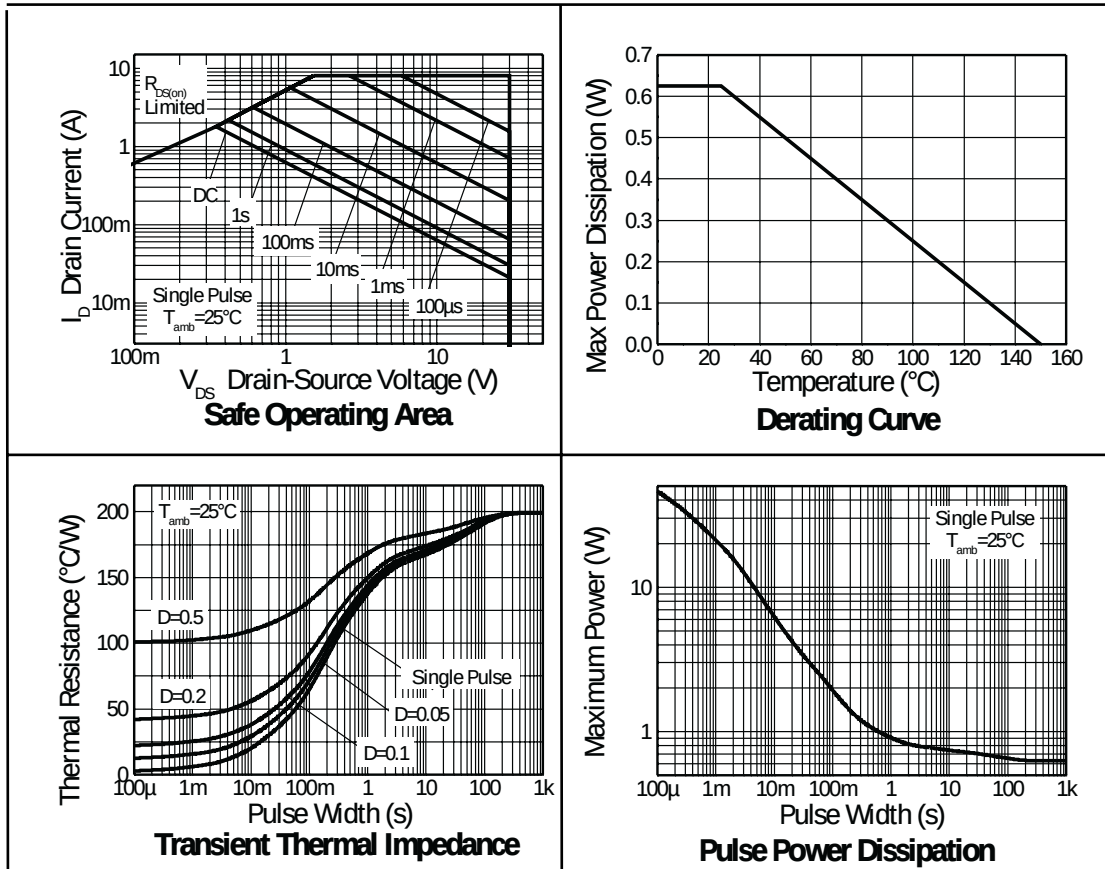
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ secs.

(c) Repetitive rating 25mm x 25mm FR4 PCB, $D = 0.05$, pulse width 10 μs - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

ZXMN3A01F

CHARACTERISTICS



ZXMN3A01F

ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise stated).

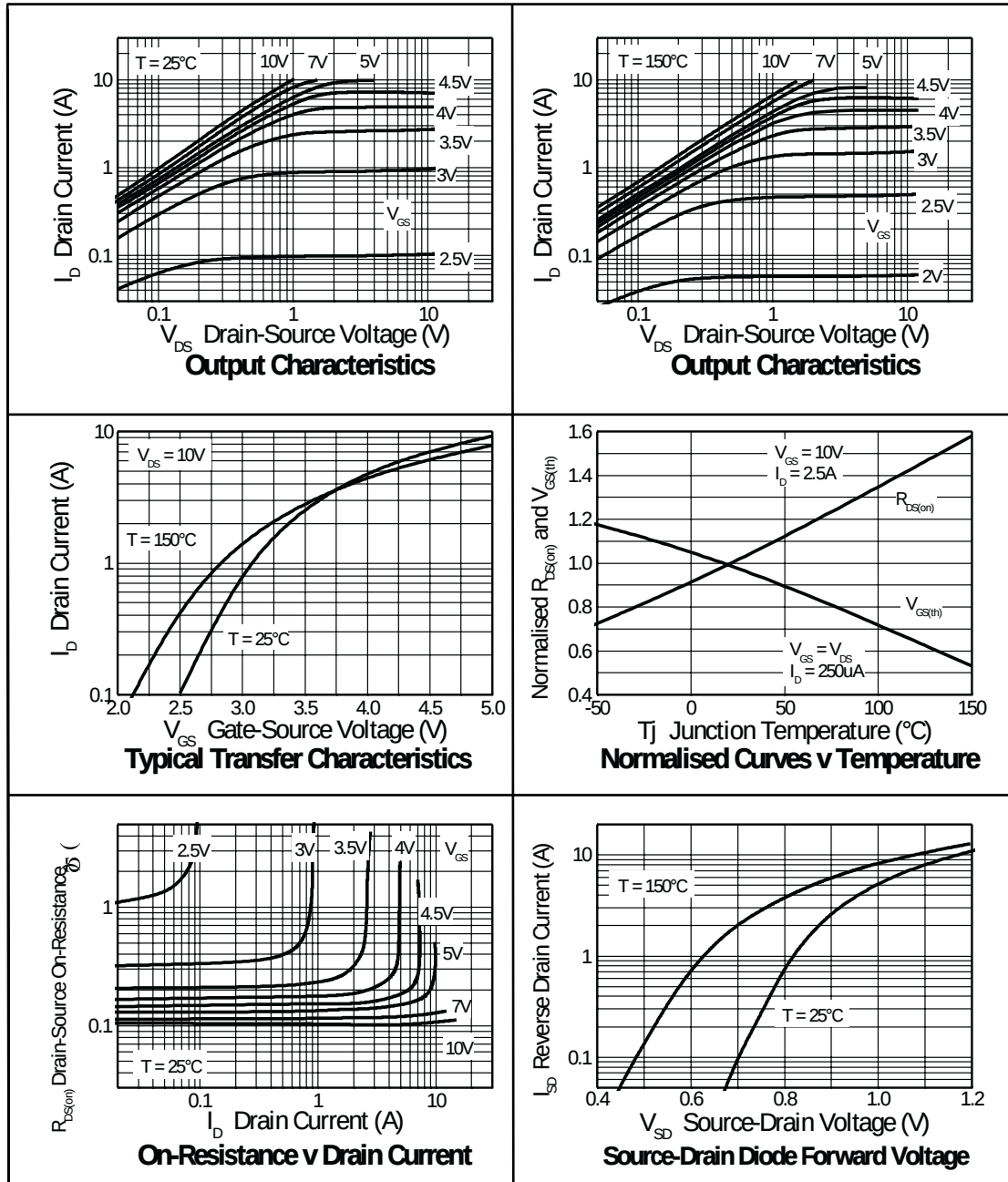
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	30			V	I _D =250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			0.5	μA	V _{DS} =30V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	1			V	I _D =250μA, V _{DS} = V _{GS}
Static Drain-Source On-State Resistance (1)	R _{DS(on)}		0.106	0.12 0.18	Ω Ω	V _{GS} =10V, I _D =2.5A V _{GS} =4.5V, I _D =2.0A
Forward Transconductance (1)(3)	g _{fs}		3.5		S	V _{DS} =4.5V,I _D =2.5A
DYNAMIC (3)						
Input Capacitance	C _{iss}		190		pF	V _{DS} =25 V, V _{GS} =0V, f=1MHz
Output Capacitance	C _{oss}		38		pF	
Reverse Transfer Capacitance	C _{rss}		20		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	t _{d(on)}		1.7		ns	V _{DD} =15V, I _D =2.5A R _G ≐6.0Ω, V _{GS} =10V
Rise Time	t _r		2.3		ns	
Turn-Off Delay Time	t _{d(off)}		6.6		ns	
Fall Time	t _f		2.9		ns	
Gate Charge	Q _g		2.3		nC	V _{DS} =15V,V _{GS} =5V, I _D =2.5A
Total Gate Charge	Q _g		3.9		nC	V _{DS} =15V,V _{GS} =10V, I _D =2.5A
Gate-Source Charge	Q _{gs}		0.6		nC	
Gate-Drain Charge	Q _{gd}		0.9		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V _{SD}		0.85	0.95	V	T _J =25°C, I _S =1.7A, V _{GS} =0V
Reverse Recovery Time (3)	t _{rr}		17.7		ns	T _J =25°C, I _F =2.5A, di/dt= 100A/μs
Reverse Recovery Charge (3)	Q _{rr}		13.0		nC	

NOTES

- (1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$.
 (2) Switching characteristics are independent of operating junction temperature.
 (3) For design aid only, not subject to production testing.

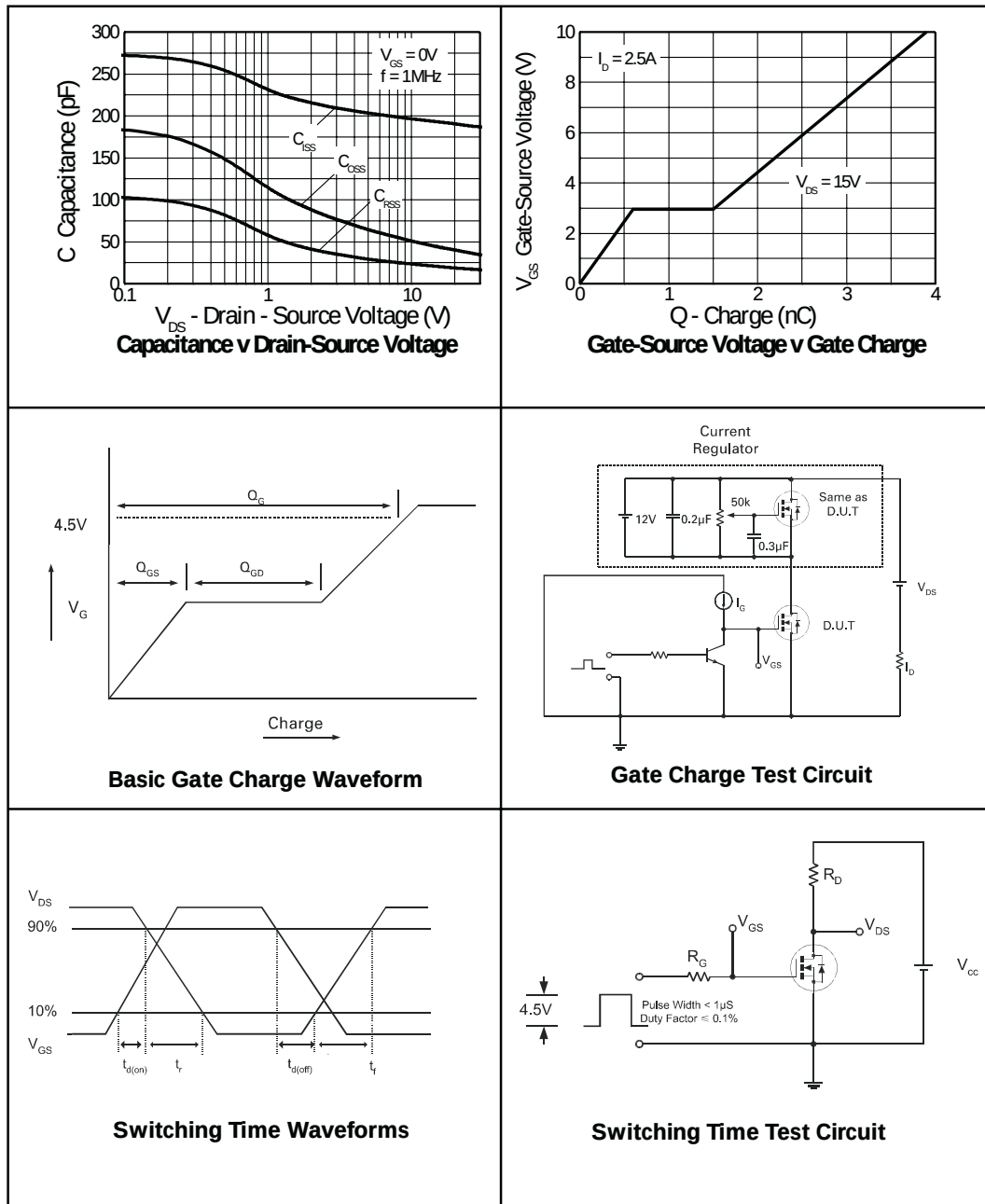
ZXMN3A01F

TYPICAL CHARACTERISTICS



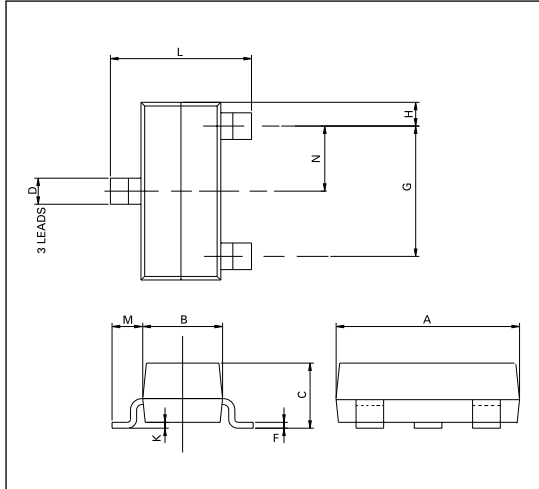
ZXMN3A01F

TYPICAL CHARACTERISTICS

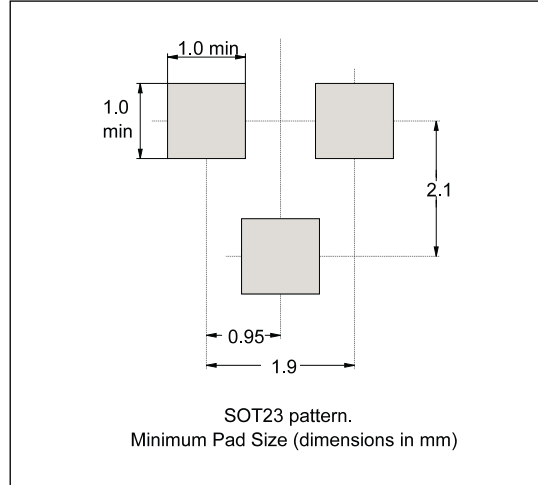


ZXMN3A01F

PACKAGE OUTLINE



PAD LAYOUT



CONTROLLING DIMENSIONS IN MILLIMETRES APPROX CONVERSIONS INCHES.

PACKAGE DIMENSIONS

DIM	MILLIMETRES		INCHES		DIM	MILLIMETRES		INCHES	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	—	1.10	—	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		φ	10° TYP		10° TYP	

© Zetex plc 2002

Europe

Zetex plc
 Fields New Road
 Chadderton
 Oldham, OL9 8NP
 United Kingdom
 Telephone: (44) 161 622 4422
 Fax: (44) 161 622 4420
 uk.sales@zetex.com

Zetex GmbH
 Streitfeldstraße 19
 D-81673 München
 Germany
 Telefon: (49) 89 45 49 49 0
 Fax: (49) 89 45 49 49 49
 europe.sales@zetex.com

Americas

Zetex Inc
 700 Veterans Memorial Hwy
 Hauppauge, NY11788
 USA
 Telephone: (631) 360 2222
 Fax: (631) 360 8222
 usa.sales@zetex.com

Asia Pacific

Zetex (Asia) Ltd
 3701-04 Metroplaza, Tower 1
 Hing Fong Road
 Kwai Fong
 Hong Kong
 Telephone: (852) 26100 611
 Fax: (852) 24250 494
 asia.sales@zetex.com

These offices are supported by agents and distributors in major countries world-wide.

This publication is issued to provide outline information only which (unless agreed by the Company in writing) may not be used, applied or reproduced for any purpose or form part of any order or contract or be regarded as a representation relating to the products or services concerned. The Company reserves the right to alter without notice the specification, design, price or conditions of supply of any product or service.

For the latest product information, log on to www.zetex.com

ISSUE 2 - JULY 2002

ZETEX